

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1077	(257/510 or 257/513).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 22:57
L2	1313	(257/647 or 257/659).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/15 23:01
L3	553	(257/395-397).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 23:06
L4	728	semiconductor and (((trench\$4 or recess\$4 or groove or STI) with ((liner or layer) near7 (top or above or over))) same ((nitride or SiN) with (cvd or (vapor adj deposit\$\$\$))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 23:18
L5	50	semiconductor and (((trench\$4 or recess\$4 or groove or STI) with ((liner) near7 (top or above or over))) same ((nitride or SiN) with (cvd or (vapor adj deposit\$\$\$))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 23:19
L6	430	semiconductor and (((trench\$4 or recess\$4 or groove or STI) with ((liner) near7 (top or above or over))) same (nitride or SiN))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/15 23:22